

Features And Application

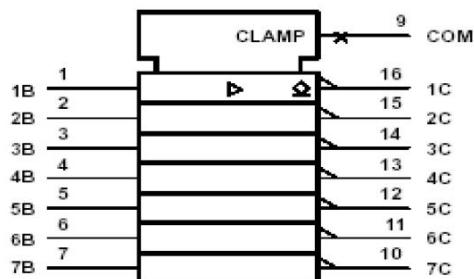
- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications

Description

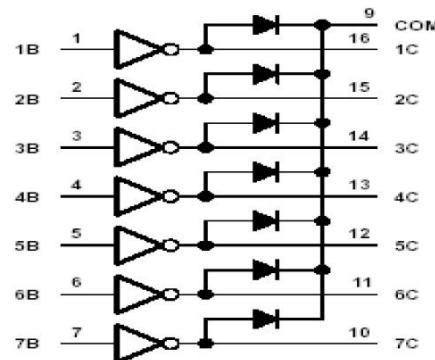
The CBM2003A are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven n-p-n Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

The CBM2003A has a 2.7-k Ω series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

LOGIC SYMBOL



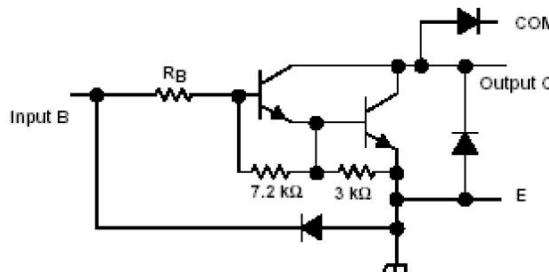
LOGIC DIAGRAM



SCHEMATICS (each Darlington Pair)

All resistor values shown are nominal.

CBM2003A: $R_B = 2.7 \text{ k}\Omega$



Absolute Maximum Ratings (Ta =25°C)

Parameter		Symbol	Limit Values		Unit
			Min.	Max.	
Output Sustaining Voltage		V _{CE(SUS)}	-0.5	50	V
Output Current		I _{OUT}	500		mA/ch
Input Voltage		V _{IN}	- 0.5	30	V
Clamp Diode Reverse Voltage		V _R	50		V
Clamp Diode Forward Current		I _F	500		mA
Power Dissipation	DIP	P _D	1.15		W
	SOP		0.95		
Operating Temperature		T _{opr}	-40	85	°C
Storage Temperature		T _{stg}	-55	150	°C

* Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied.

Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Recommended Operating Conditions(Ta=-40~85°C)

Parameter		Symbol	Test Condition	Limit Value		Unit	
				Min	Max		
Output Sustaining Voltage		V _{CE(SUS)}		0	50	V	
Output Current	DIP	I _{OUT}	Tpw=25ms,Duty=10%, 7 Circuits	0	370	mA/ch	
			Tpw=25ms,Duty=30%, 7 Circuits	0	200		
			Tpw=25ms,Duty=10%, 7 Circuits	0	390		
			Tpw=25ms,Duty=30%, 7 Circuits	0	150		
Input Voltage		V _{IN}		0	3.	V	
Clamp Diode Reverse Voltage		V _R			50	V	
Clamp Diode Forward Current		I _F			400	mA	
Power Dissipation	DIP	P _D			0.52	W	
	SOP				0.4		

Electrical Characteristics ,Ta= 25°C (unless otherwise noted)

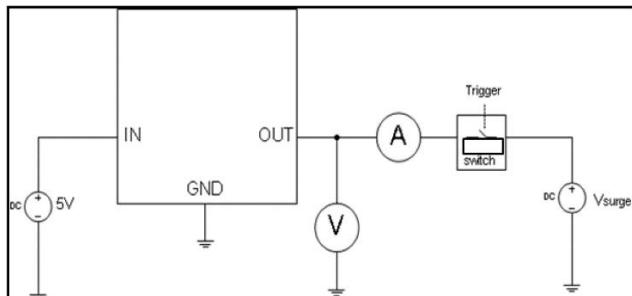
Parameter		Test Fig.	Test Conditions		Min	Typ	Max	Unit
$V_{I(on)}$	On-state Input Voltage	6	$V_{CE}=2V$	$I_C=125mA$				V
				$I_C=200mA$			2.4	
				$I_C=250mA$			2.7	
				$I_C=275mA$				
				$I_C=300mA$			3	
				$I_C=350mA$				
$V_{CE(sat)}$	Collector-emitter saturation voltage	5	$I_I=250\mu A$	$I_C=100mA$		0.9	1.1	V
			$I_I=350\mu A$	$I_C=200mA$		1	1.3	
			$I_I=500\mu A$	$I_C=350mA$		1.2	1.6	
I_{CEX}	Collector outoff current	1	$V_{CE}=50V$	$I_I=0$			50	uA
		2	$V_{CE}=50V,$ $T_A=85^\circ C$	$I_I=0$			100	
h_{FE}	DC Current Transfer Ratio	5	$V_{CE}=2V, I_{OUT}=350mA$		1000			
V_F	Clamp forward voltage	8	$I_F=350mA$			1.7	2	V
$I_{I(off)}$	Off-state input current	3	$V_{CE}=50V$ $T_A=85^\circ C$	$I_C=500\mu A$	50	65		uA
I_I	Input current	4	$V_I=2.4V$			0.4	0.7	mA
			$V_I=5V$					
			$V_I=12V$					
I_R	Clamp reverse current	7	$V_R=50V$				50	uA
			$V_R=50V$	$T_A=85^\circ C$			100	
C_I	Input capacitance		$V_I=0$	$f=1MHz$		15	25	pF

Switching Characteristics, TA=25°C

Parameter		Test Conditions	Min	Typ	Max	Unit
t_{PLH}	Propagation delay time, low-to-high-level output	See Figure 9		0.25	1	us
t_{PHL}	Propagation delay time, high -to- low –level output			0.25	1	us
V_{OH}	High-level output voltage after switching		$V_S=50V, IO=300mA$, See Figure 10	V_S-20		mV

* EOS (Electrical Over Stress) Immunity Level

Test Circuit



Test conditions	
VCC	12V
Power on time	5000ms
Current max	1.0A
IN	pin4
OUT	pin13

tE (Endurance time) : time until IC damage / Criterion : IC should survive EOS

EOS Immunity Level: More than 5000ms

PARAMETER MEASUREMENT INFORMATION

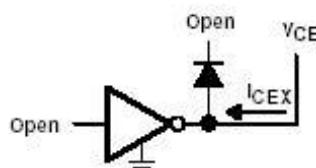


Figure 1. I_{CEx} Test Circuit

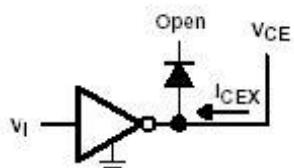


Figure 2. I_{CEx} Test Circuit

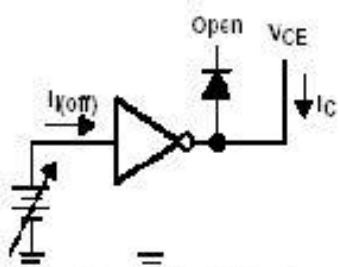


Figure 3. $I_{(off)}$ Test Circuit

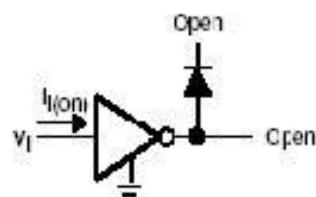
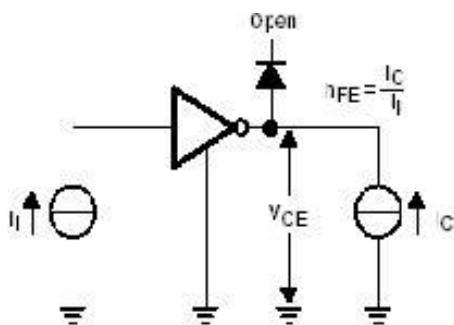


Figure 4. I_I Test Circuit



NOTE: I_I is fixed for measuring $V_{CE}(\text{sat})$, variable for measuring h_{FE} .

Figure 5. h_{FE} , $V_{CE}(\text{sat})$ Test Circuit

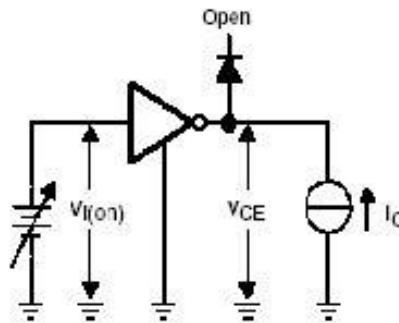


Figure 6. $V_{I(on)}$ Test Circuit

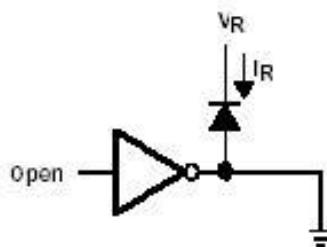


Figure 7. I_R Test Circuit

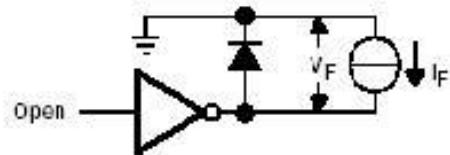


Figure 8. V_F Test Circuit

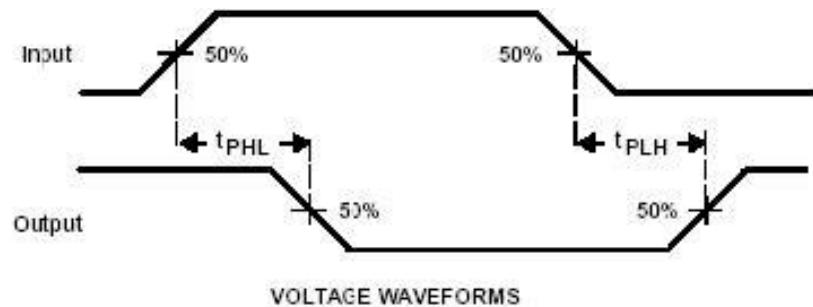


Figure 9. Propagation Delay-Time Waveforms

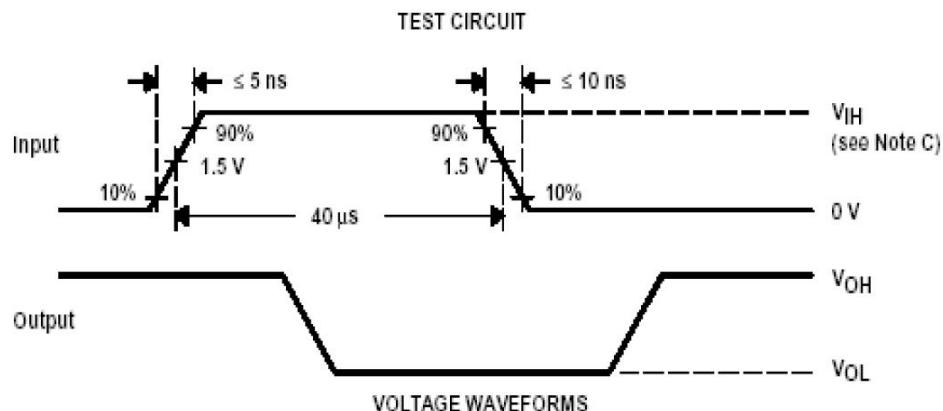


Figure 10. Latch-Up Test Circuit and Voltage Waveforms

NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_0=50$.

- B. CL includes probe and jig capacitance.
- C. $VIH = 3$ V;

TYPICAL CHARACTERISTICS

**COLLECTOR-EMITTER
SATURATION VOLTAGE
vs
COLLECTOR CURRENT
(ONE DARLINGTON)**

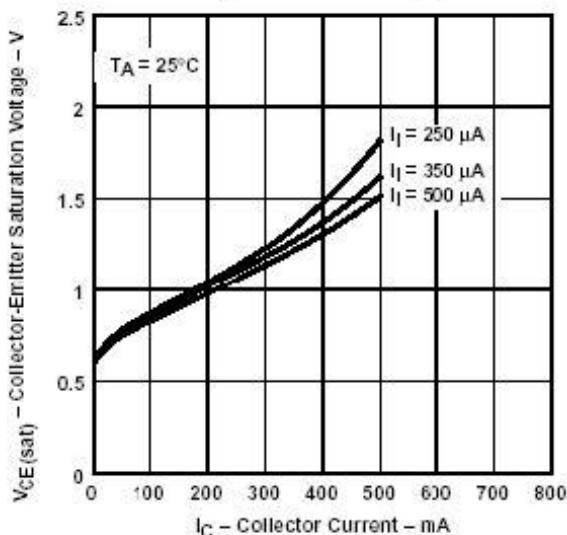


Figure 11

**COLLECTOR-EMITTER
SATURATION VOLTAGE
vs
TOTAL COLLECTOR CURRENT
(TWO DARLINGTONS PARALLELED)**

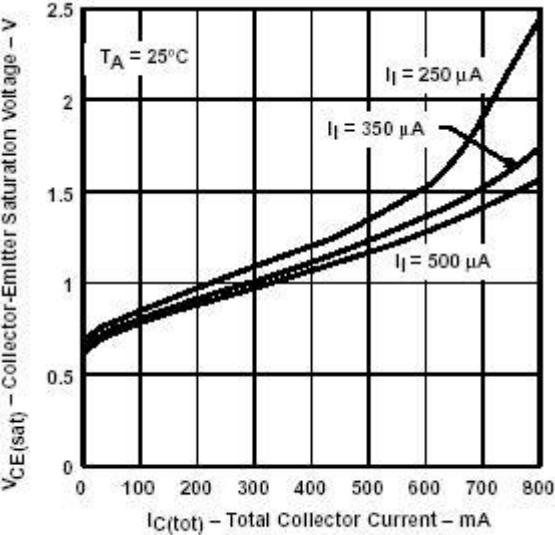


Figure 12

**COLLECTOR CURRENT
vs
INPUT CURRENT**

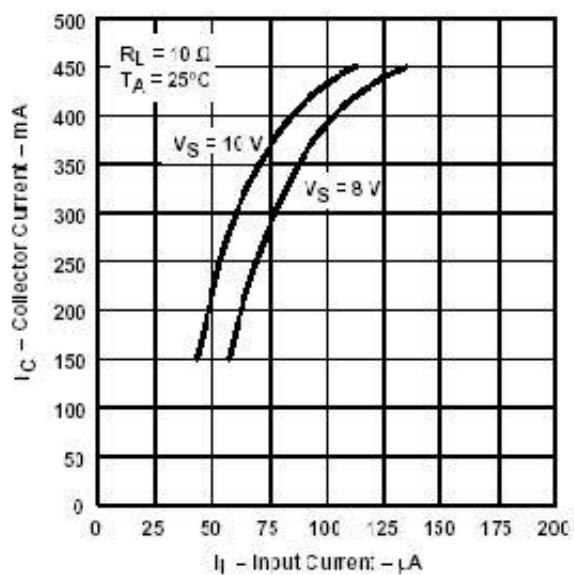


Figure 13

THERMAL INFORMATION

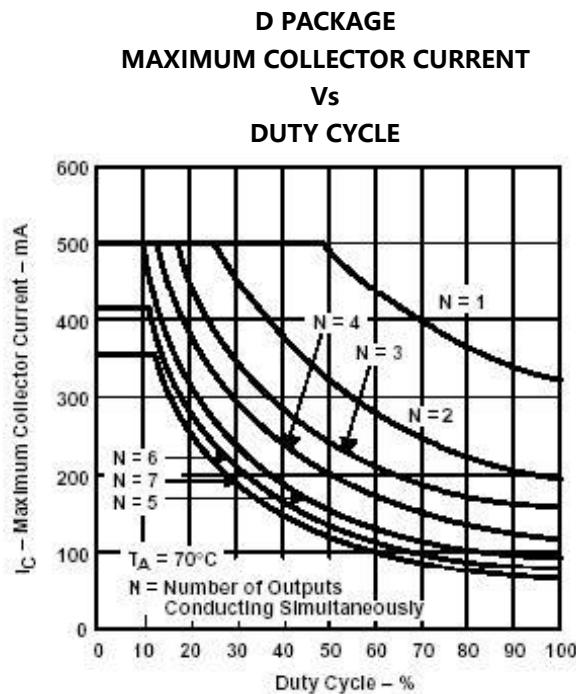


Figure 14

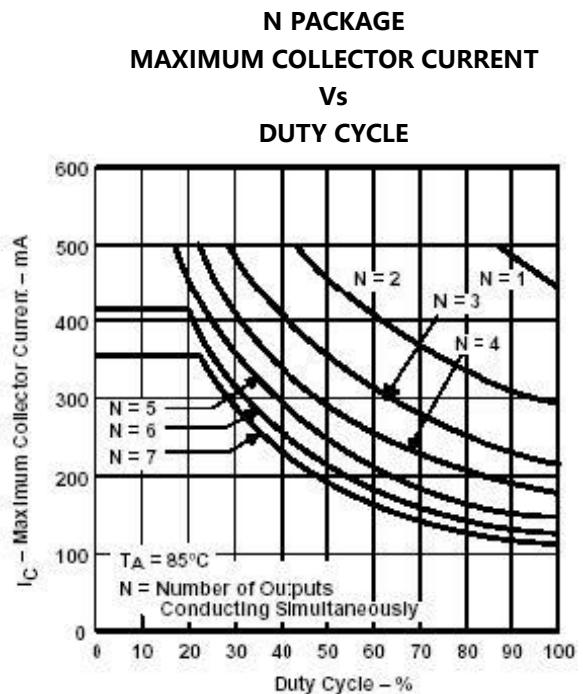
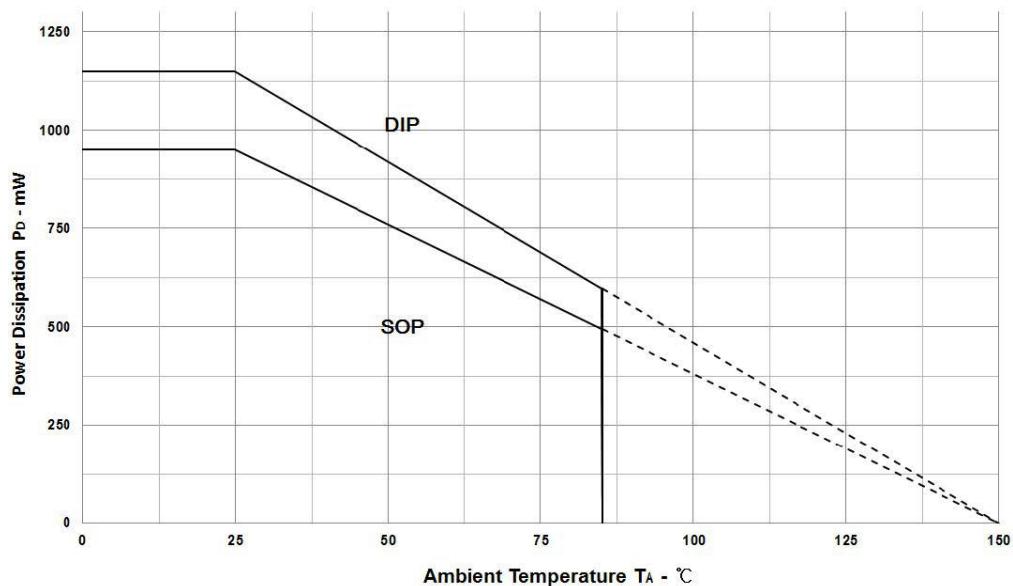


Figure 15

POWER DISSIPATION

VS.

AMBIENT TEMPERATURE



APPLICATION INFORMATION

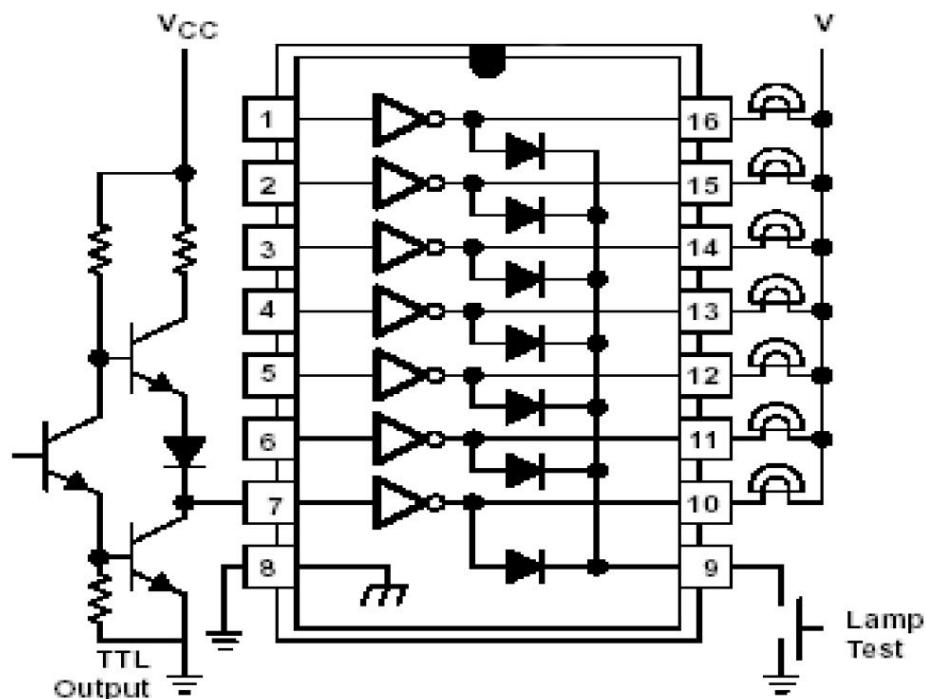


Figure 16. TTL to Load

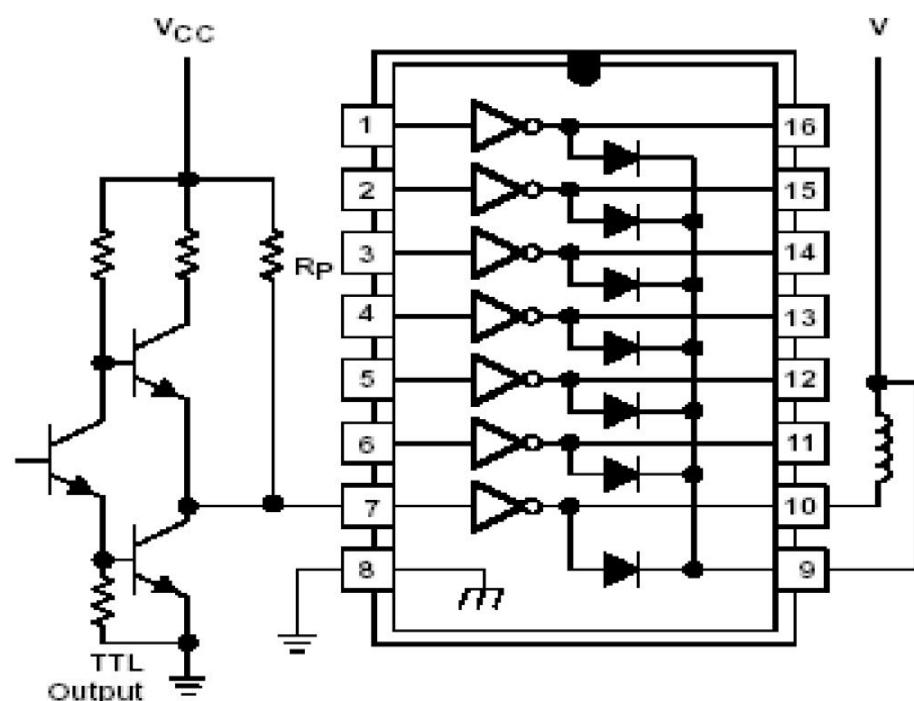
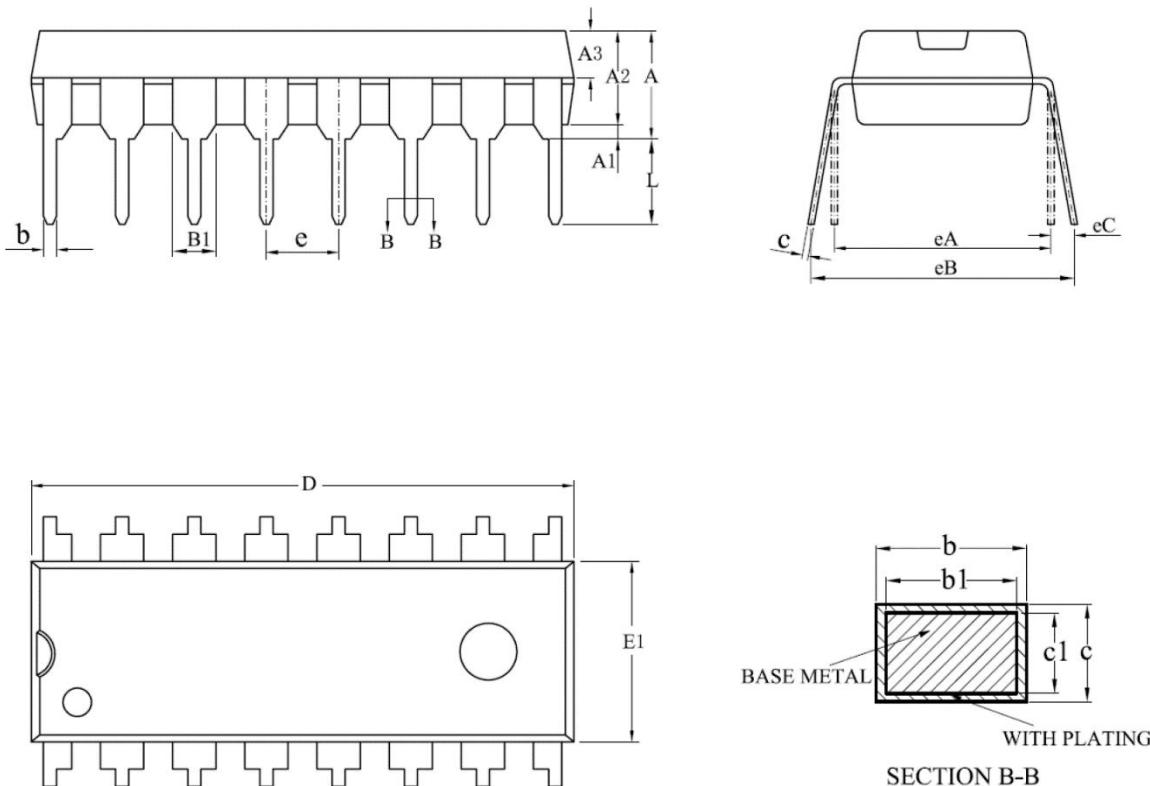


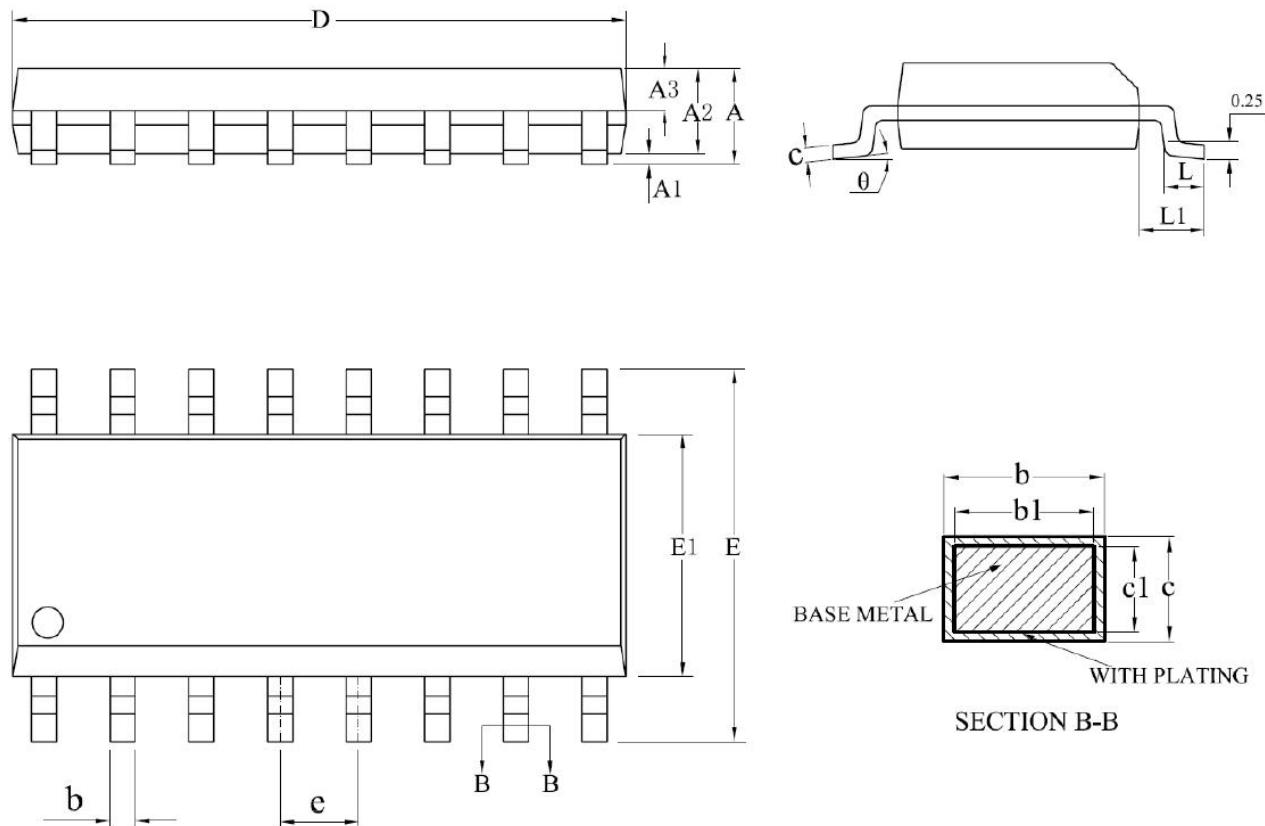
Figure 17. Use of Pullup Resistors to Increase Drive Current

Package Dimensions

DIP-16



SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	NOM	MAX		MIN	NOM	MAX
A	3.60	3.80	4.00	c1	0.24	0.25	0.26
A1	0.51			D	18.90	19.10	19.30
A2	3.10	3.30	3.50	E1	6.15	6.35	6.55
A3	1.42	1.52	1.62	e	2.54 BSC		
b	0.44		0.53	eA	7.62 BSC		
b1	0.43	0.46	0.48	eB	7.62		9.50
B1	1.52 BSC			eC	0		0.94
c	0.25		0.31	L	3.00		
L/F 载体尺寸 (Mil)	80×80						
	110×140						
	140×170						

SOP-16


SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	NOM	MAX		MIN	NOM	MAX
A			1.75	D	9.70	9.90	10.10
A1	0.10		0.25	E	5.80	6.00	6.20
A2	1.35	1.40	1.45	E1	3.70	3.90	4.10
A3	0.60	0.65	0.70	e	1.27 BSC		
b	0.39		0.48	L	0.50		0.80
b1	0.38	0.41	0.43	L1	1.05 BSC		
c	0.21		0.26	θ	0°		8°
c1	0.19	0.20	0.21				
L/F 载体尺寸 (Mil)	75×75						
	90×110						
	70×180						

PACKAGE/ORDERING INFORMATION

PRODUCT	ORDERING	TEMPRANGE	PACKAGE	PAKEAGE	TRANSPOT
CBM2003	CBM2003AS	-40°C~85°C	SOP-16	CBM2003A	Tape and Reel,2500
CBM2003	CBM2003AIP	-40°C~85°C	DIP-16	CBM2003AIP	Tape and Reel,50